

etching the second portion of the second interlayer dielectric layer overlying the gap, the first portion of the second interlayer dielectric layer occupying the gap in the conductive line, and [a] the portion of the first interlayer dielectric layer [underlying the gap in] overlying the conductive [line] region, using the photosensitive film pattern and the conductive line as etch masks.

1 11. (Amended) The method of claim 9, wherein the etching of the first and  
2 second interlayer dielectric layers comprises:

etching the second portion of the second interlayer dielectric layer using the photosensitive film pattern as an etch mask until a portion of the conductive line defining the gap is exposed, and

discretely etching the first portion of the second interlayer dielectric layer occupying the gap in the conductive line, and the portion of the first interlayer dielectric layer underlying the gap, using the etched second interlayer dielectric layer and the portion of the conductive line defining the gap therein as etch masks.

1 12. (Amended) The method of claim 9, wherein the [etching] forming of the  
2 portion of the conductive line defining the gap therein comprises an anisotropic etching  
3 process which produces inclined sidewalls therein, whereby the cross-sectional area of an upper portion of the contact hole is greater than that of a lower portion thereof.